**Product data sheet** 

## 1. Product profile

#### 1.1 General description

Planar passivated very sensitive gate four quadrant triac in a SOT223 (SC-73) surface-mountable plastic package intended for applications requiring direct interfacing to logic level ICs and low power gate drivers.

#### 1.2 Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drive circuits
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants
- Very sensitive gate

#### 1.3 Applications

- General purpose low power motor control
- Home appliances

- Industrial process control
- Low power AC Fan controllers

#### 1.4 Quick reference data

Table 1. Quick reference data

| Symbol              | Parameter                            | Conditions  | Min | Тур | Max | Unit |
|---------------------|--------------------------------------|---|-----|-----|-----|------|
| $V_{DRM}$           | repetitive peak off-state voltage    |   | -   | -   | 800 | V    |
| I <sub>TSM</sub>    | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25$ °C;<br>$t_p = 20$ ms; see Figure 4;<br>see Figure 5                              | -   | -   | 8   | Α    |
| I <sub>T(RMS)</sub> | RMS on-state current                 | full sine wave; $T_{sp} \le 105 ^{\circ}\text{C}$ ; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u> | -   | -   | 1   | Α    |



**4Q Triac** 

Table 1. Quick reference data ...continued

| Idbio II        | Quion reference data : | oonanada   |     |     |     |      |
|-----------------|------------------------|--|-----|-----|-----|------|
| Symbol          | Parameter              | Conditions   | Min | Тур | Max | Unit |
| Static cha      | aracteristics          |  |     |     |     |      |
| I <sub>GT</sub> | gate trigger current   | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+G+;$<br>$T_j = 25 \text{ °C; see } \frac{\text{Figure 8}}{\text{ C; }}$             | -   | -   | 5   | mA   |
|                 |                        | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$<br>$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$         | -   | -   | 5   | mA   |
|                 |                        | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$<br>$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{\text{Im}}$ | -   | -   | 5   | mA   |
|                 |                        | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$<br>$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{\text{I}}$         | -   | -   | 7   | mA   |

# 2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description     | Simplified outline | Graphic symbol |
|-----|--------|-----------------|--------------------|----------------|
| 1   | T1     | main terminal 1 |                    | <b>N</b> .     |
| 2   | T2     | main terminal 2 | 4                  | T2—            |
| 3   | G      | gate            |                    | `G<br>sym051   |
| 4   | T2     | main terminal 2 | 1 2 3              |                |
|     |        |                 | SOT223 (SOT223)    |                |

# 3. Ordering information

Table 3. Ordering information

| Type number | Package |  |         |  |
|-------------|---------|--|---------|--|
|             | Name    | Description  | Version |  |
| Z0107NN     | SOT223  | plastic surface-mounted package with increased heatsink; 4 leads | SOT223  |  |

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# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                         | Parameter                            | Conditions  | Min | Max  | Unit   |
|--------------------------------|--------------------------------------|---|-----|------|--------|
| $V_{DRM}$                      | repetitive peak off-state voltage    |   | -   | 800  | V      |
| I <sub>T(RMS)</sub>            | RMS on-state current                 | full sine wave; $T_{sp} \le 105$ °C; see Figure 3; see Figure 1; see Figure 2                                     | -   | 1    | Α      |
| I <sub>TSM</sub>               | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; see <u>Figure 4</u> ; see <u>Figure 5</u> | -   | 8    | Α      |
|                                |                                      | full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$   | -   | 8.5  | Α      |
| l <sup>2</sup> t               | I <sup>2</sup> t for fusing          | $t_p = 10 \text{ ms}$ ; sine-wave pulse   | -   | 0.32 | $A^2s$ |
| dl <sub>T</sub> /dt rate of ri | rate of rise of on-state current     | $I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.1 A/ $\mu$ s; T2+ G+  | -   | 50   | A/µs   |
|                                |                                      | $I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.1 A/ $\mu$ s; T2+ G-  | -   | 50   | A/µs   |
|                                |                                      | $I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.1 A/ $\mu$ s; T2- G-  | -   | 50   | A/µs   |
|                                |                                      | $I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.1 A/ $\mu$ s; T2- G+  | -   | 20   | A/µs   |
| I <sub>GM</sub>                | peak gate current                    |   | -   | 1    | Α      |
| P <sub>GM</sub>                | peak gate power                      |   | -   | 2    | W      |
| P <sub>G(AV)</sub>             | average gate power                   | over any 20 ms period   | -   | 0.1  | W      |
| T <sub>stg</sub>               | storage temperature                  |   | -40 | 150  | °C     |
| T <sub>j</sub>                 | junction temperature                 |   | -   | 125  | °C     |

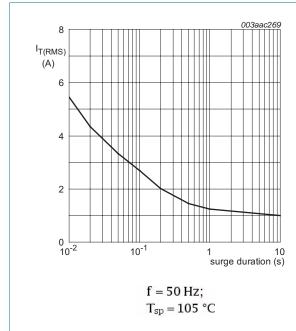


Fig 1. RMS on-state current as a function of surge duration; maximum values

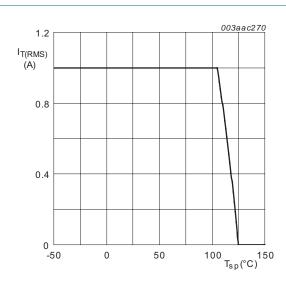


Fig 2. RMS on-state current as a function of solder point temperature; maximum values

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4Q Triad

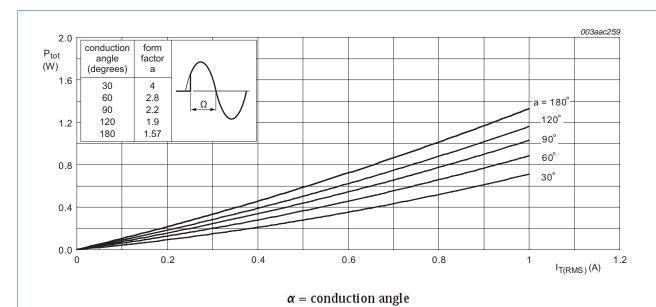


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

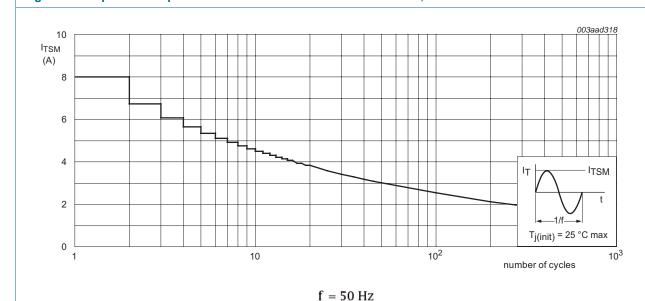
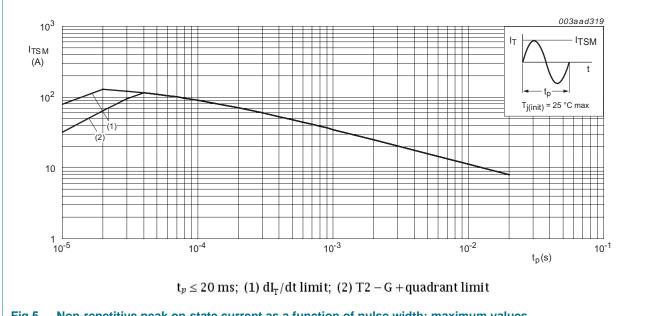


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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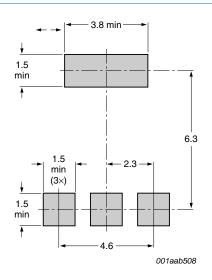
Non-repetitive peak on-state current as a function of pulse width; maximum values

**4Q Triac** 

## 5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol         | Parameter  | Conditions   | Min | Тур | Max | Unit |
|----------------|--|--|-----|-----|-----|------|
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | full cycle; see Figure 7   | -   | -   | 15  | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient      | full cycle; printed circuit board mounted; minimum footprint; see Figure 6 | -   | 156 | -   | K/W  |
|                |  | full cycle; printed circuit board mounted; pad area; see Figure 6          | -   | 70  | -   | K/W  |



All dimensions are in mm

Fig 6. Minimum footprint SOT223

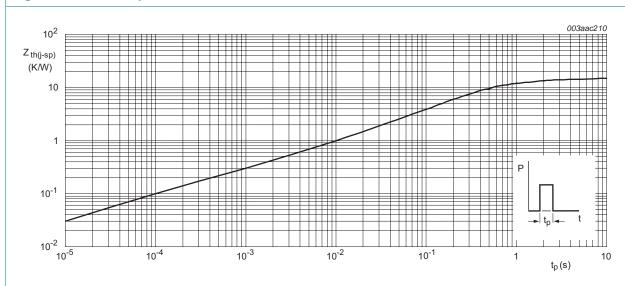


Fig 7. Transient thermal impedance from junction to solder point as a junction of pulse width

Z0107NN

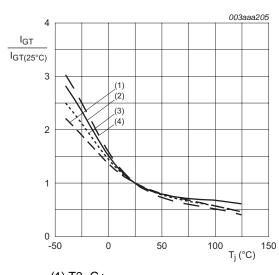
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# 6. Characteristics

#### Table 6. Characteristics

| Symbol                | Parameter                             | Conditions  | Min | Тур | Max | Unit |
|-----------------------|---------------------------------------|---|-----|-----|-----|------|
| Static chara          | acteristics                           |   |     |     |     |      |
| I <sub>GT</sub>       | gate trigger current                  | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$<br>$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$                  | -   | -   | 5   | mA   |
|                       |                                       | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-; T_j = 25 \text{ °C;}$ see Figure 8   | -   | -   | 5   | mA   |
|                       |                                       | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- }G\text{-; } T_j = 25 ^{\circ}\text{C;}$ see Figure 8                         | -   | -   | 5   | mA   |
|                       |                                       | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{-}G+; T_j = 25 \text{ °C;}$ see Figure 8  | -   | -   | 7   | mA   |
| I <sub>L</sub>        | latching current                      | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$<br>$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{}$                  | -   | -   | 10  | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$<br>$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{}$                  | -   | -   | 20  | mA   |
|                       |                                       | $V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2\text{- }G\text{-; } T_j = 25 ^{\circ}\text{C;}$ see Figure 9                         | -   | -   | 10  | mA   |
|                       |                                       | $V_D = 12 \text{ V; } I_G = 0.1 \text{ A; T2- G+;}$<br>$T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{\text{ or other seconds}}$ | -   | -   | 10  | mA   |
| l <sub>H</sub>        | holding current                       | $V_D = 12 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 10}{}$  | -   | -   | 10  | mΑ   |
| V <sub>T</sub>        | on-state voltage                      | $I_T = 1.4 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 11}{\text{Model}}$                                     | -   | 1.3 | 1.6 | V    |
| $V_{GT}$              | gate trigger voltage                  | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T_j = 25 \text{ °C;}$<br>see Figure 12  | -   | -   | 1.3 | V    |
|                       |                                       | $V_D = 800 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ see <u>Figure 14</u>  | 0.2 | -   | -   | V    |
| I <sub>D</sub>        | off-state current                     | $V_D = 800 \text{ V}; T_j = 125 ^{\circ}\text{C}$   | -   | -   | 0.5 | mΑ   |
| Dynamic ch            | naracteristics                        |   |     |     |     |      |
| dV <sub>D</sub> /dt   | rate of rise of off-state voltage     | $V_{DM}$ = 536 V; $T_j$ = 110 °C; gate open circuit; exponential waveform; see Figure 13  | 20  | -   | -   | V/µs |
| dV <sub>com</sub> /dt | rate of change of commutating voltage | $V_D = 400 \text{ V}$ ; $T_j = 110 ^{\circ}\text{C}$ ; $dI_{com}/dt = 0.44 \text{A/ms}$ ; gate open circuit                         | 1   | -   | -   | V/µs |
|                       |                                       |   |     |     |     |      |

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- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig 8. Normalized gate trigger current as a function of junction temperature

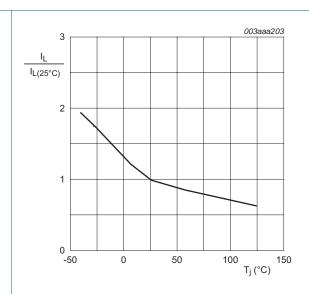


Fig 9. Normalized latching current as a function of junction temperature

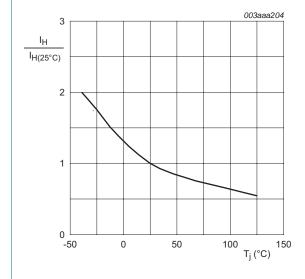
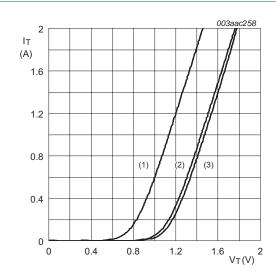


Fig 10. Normalized holding current as a function of junction temperature



 $V_0 = 1.13 \text{ V}$ 

 $R_s = 0.31 \Omega$ 

(1) T<sub>i</sub> = 125 °C; typical values

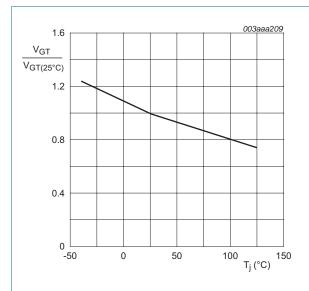
(2) T<sub>j</sub> = 125 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig 11. On-state current as a function of on-state voltage

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1.6 1.2 0.8 0.4 0 T<sub>i</sub> (°C)

$$A = \frac{dV_D/dt}{dV_{D(25^{\circ}C)}/dt}$$

Fig 12. Normalized gate trigger voltage as a function of junction temperature

Fig 13. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

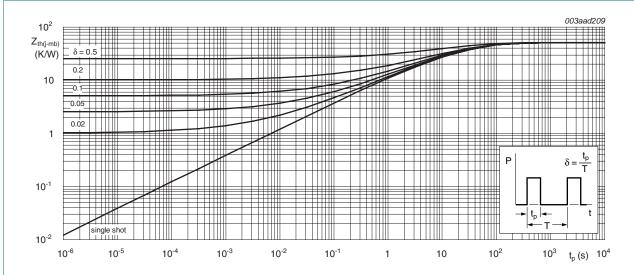


Fig 14. Transient thermal impedance from junction to ambient as a function of pulse duration, FET2 (PCB used for thermal tests; heat sink area 400mm2)

# 7. Package outline

### Plastic surface-mounted package with increased heatsink; 4 leads **SOT223** В - A = v M A a **→** | w (M) B detail X е 4 mm scale **DIMENSIONS** (mm are the original dimensions) $\mathbf{H}_{\mathsf{E}}$ UNIT $A_1$ $\mathbf{b}_{\mathbf{p}}$ b<sub>1</sub> С Ε Q е e<sub>1</sub> $L_{p}$ у 1.8 0.10 0.80 0.32 0.95 2.3 4.6 0.2 0.1 0.1 0.01 3.3 REFERENCES OUTLINE VERSION EUROPEAN **ISSUE DATE PROJECTION** IEC **JEDEC** JEITA 04-11-10 SOT223 SC-73 06-03-16

Fig 15. Package outline SOT223 (SOT223)

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8. Revision history

## Table 7. Revision history

| Document ID    | Release date                      | Data sheet status  | Change notice | Supersedes  |
|----------------|-----------------------------------|--------------------|---------------|-------------|
| Z0107NN v.5    | 20110322                          | Product data sheet | -             | Z0107NN v.4 |
| Modifications: | <ul> <li>Various chang</li> </ul> | es to content.     |               |             |
| Z0107NN v.4    | 20100906                          | Product data sheet | -             | Z0107NN v.3 |

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## 9. Legal information

#### 9.1 Data sheet status

| Document status [1] [2]        | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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